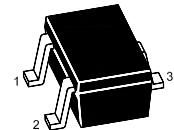


TRANSISTOR (NPN)

FEATURE

Excellent h_{FE} Linearity Low noise

Complementary to A733W



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

MARKING: CR

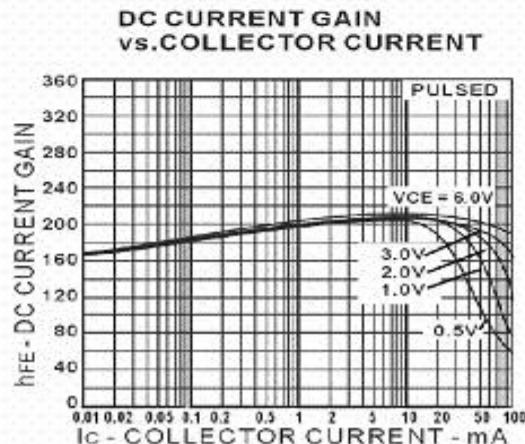
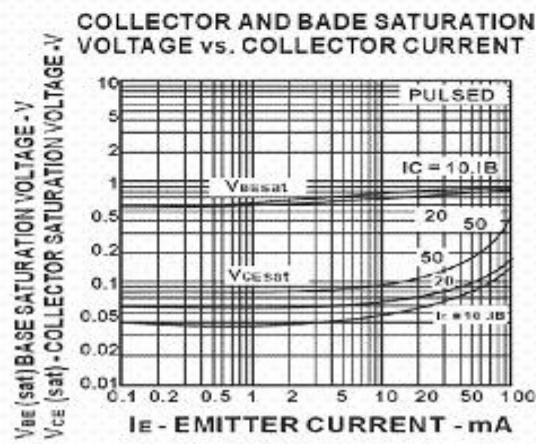
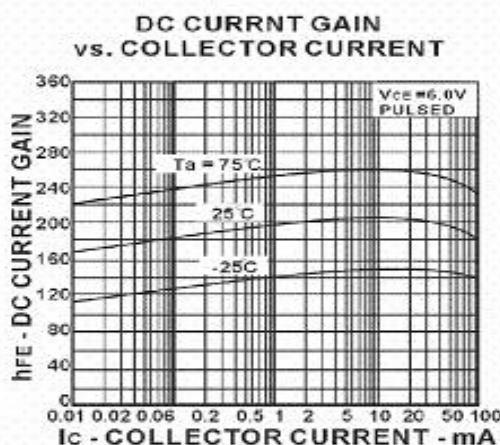
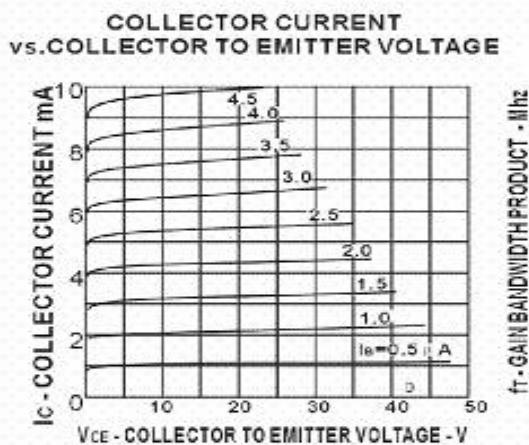
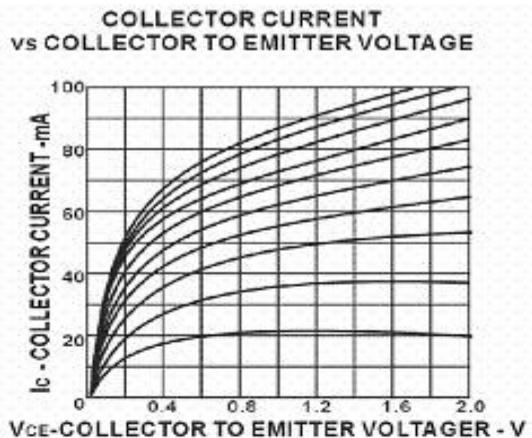
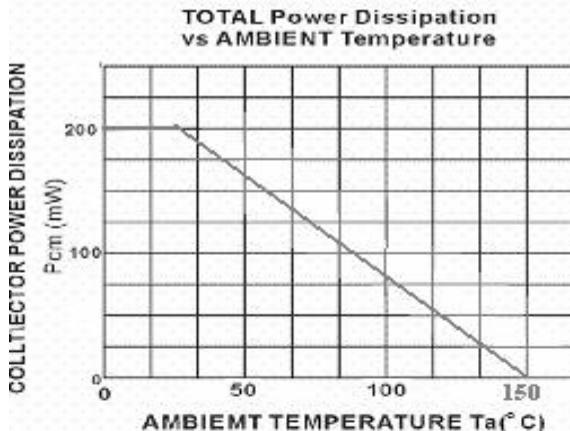
MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	150	mA
P_c	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	°C
T_{sta}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ C$ unless otherwise specified)

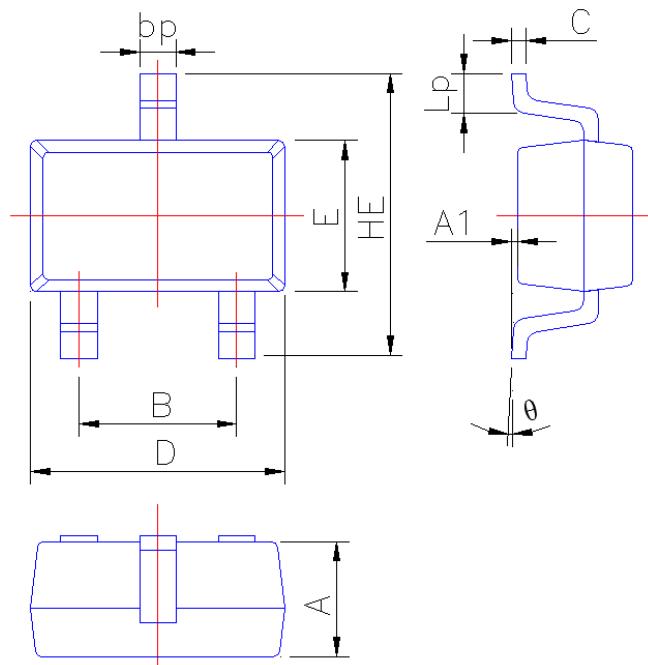
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=0.1mA, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Collector cut-off current	I_{CER}	$V_{CE}=55V, R=10M\Omega$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_C=1mA$	200		400	
	$h_{FE(2)}$	$V_{CE}=6V, I_C=0.1mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=6V, I_C=10mA, f=30\text{ MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			3.0	pF
Noise figure	NF	$V_{CE}=6V, I_C=0.1mA$ $R_g=10k\Omega, f=1kMHz$		4	10	dB

Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°